NSN 5961-01-087-7226

A110a0

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-087-7226 **Inclosure Material:** Metal **Overall Length:** 0.165 inches **Overall Diameter:** 0.200 inches **Component Name And Quantity:** 2 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 60.0 collector to base voltage, dc all transistor and 30.0 collector to emitter voltage, dc all transistor and 5.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 500.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 1.6 watts small-signal input power, common-collector preset all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius ambient air **Special Features:** All transistor junction pattern arrangement: npn **Test Data Document:** 97942-581r870 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 6 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: